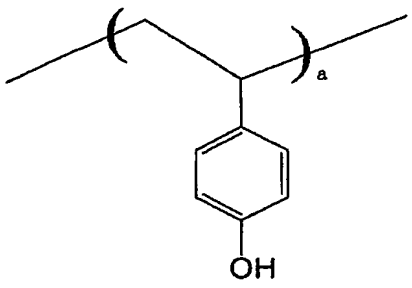
WHAT IS CLAIMED IS:

1. An organic anti-reflective composition comprising a crosslinking agent, a light absorbing agent, a thermal acid generator, an organic solvent and an adhesivity enhancer represented by the following Chemical Formula 1:

Chemical Formula 1



wherein

a is the degree of polymerization, ranging from 30 to 400.

2. The organic anti-reflective composition according to Claim 1, which comprises:

(a) 100 parts by weight of crosslinking agent;

(b) 30 to 400 parts by weight of light absorbing agent;

(c) 10 to 200 parts by weight thermal acid generator;

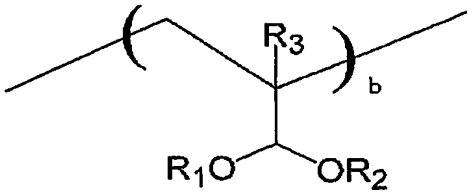
(d) 30 to 400 parts by weight of adhesivity enhancer represented by Chemical Formula 1; and

(e) 1,000 to 10,000 parts by weight of organic solvent.

3. The organic anti-reflective composition according to Claim 2, wherein said

crosslinking agent is the compound represented by the following Chemical Formula 2:

Chemical Formula 2



wherein

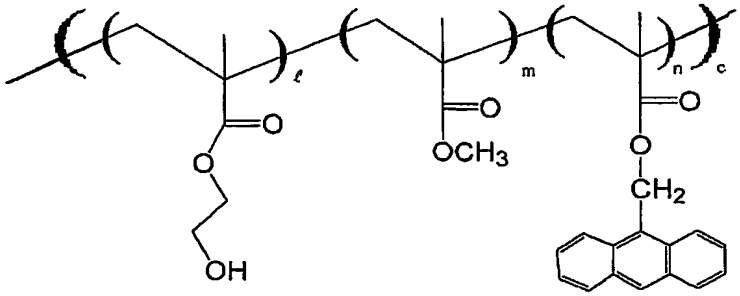
b is the degree of polymerization, ranging from 10 to 100;

each of R_1 and R_2 is C_1 to C_4 alkyl; and

R_3 is hydrogen or methyl.

4. The organic anti-reflective composition according to Claim 2, wherein said light absorbing agent is the compound represented by the following Chemical Formula 3:

Chemical Formula 3



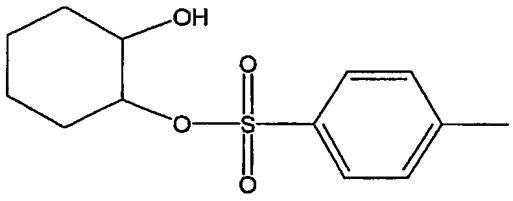
wherein

ℓ, m and n are molar ratios: ℓ ranging from 0.1 to 0.5, m ranging from 0.05 to 0.5, n ranging from 0.1 to 0.7, and ℓ + m + n = 1; and

c is the degree of polymerization, ranging from 10 to 400.

5. The organic anti-reflective composition according to Claim 2, wherein said thermal acid generator is the compound represented by the following Chemical Formula 4:

Chemical Formula 4



6. A patterning method comprising the steps of

(a) coating the organic anti-reflective composition according to Claim 1 on a part to be etched;

(b) crosslinking said organic anti-reflective composition by baking to form an organic anti-reflective film;

(c) coating a photoresist on said organic anti-reflective film, and exposing and developing the same to form a photoresist pattern; and

(d) etching the organic anti-reflective film with said photoresist pattern as mask.

7. The patterning method according to Claim 6, wherein said baking of the step (b) is carried out at 150 to 300 ℃ for 1 to 5 minutes.

8. The patterning method according to Claim 6, wherein baking is further carried out before and/or after exposure of the step (c).

9. The patterning method according to Claim 8, wherein said baking is carried out

at 70 to 200 ℃.

10. The patterning method according to Claim 6, wherein far UV such as F_2 laser (157 nm), ArF (193 nm), KrF (248 nm) and EUV (extremely ultraviolet); E-beam; X-ray; or ion beam is used as exposure light source in the step (c).

11. A semiconductor device prepared by any method according to Claims 6 to 10.